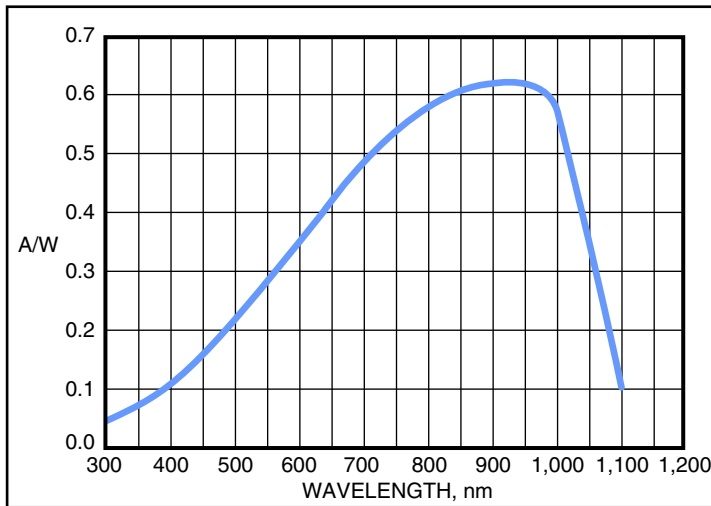


# DATA SHEET

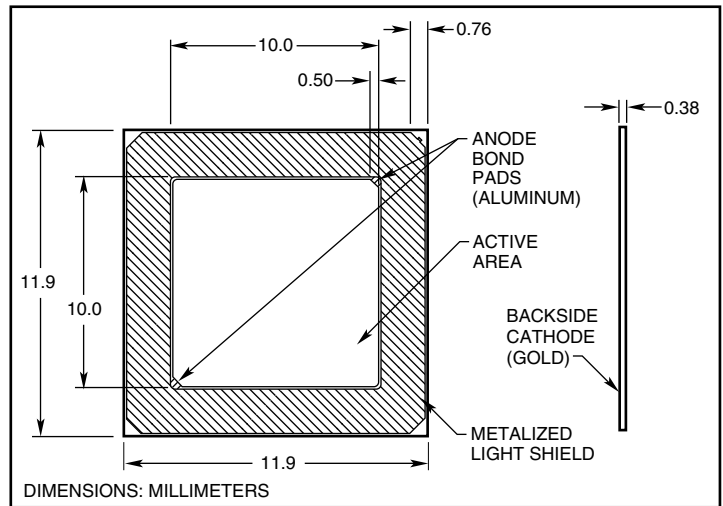
# PSS100-7-C

## LARGE AREA SILICON PHOTODIODE PSS100-7-C

PSS100-7-C has an active area of 100 mm<sup>2</sup> and features very low capacitance for its size (12 pF at 80 volts bias). The active area is surrounded by a reflective aluminum stripe that prevents illumination of the so-called "dead" silicon. This improves the speed of response. The die may be mounted in hermetically sealed packages or it is now available in our surface mounting assemble illustrated on the next page. (Please see PSS100-7-SM).



**SPECTRAL RESPONSE**



**OUTLINE DIMENSIONS**

### PHOTODIODE CHARACTERISTICS PER SEGMENT

PART NO.	ACTIVE AREA mm <sup>2</sup>	ACTIVE AREA (size) mm	DARK CURRENT nA @ 12V		CAPACITANCE PF @		RISE TIME ns @ 850 nm	NEP W/H <sup>1/2</sup> OV @ 663 nm
			TYP	MAX	0V	12V		
PSS100-7-C	100	10 X 10	0.5	5.0	240	80*	55 @ 12 V	6* 10 <sup>-14</sup>

### ABSOLUTE MAXIMUM RATINGS

DC REVERSE VOLTAGE	PEAK DC CURRENT	STORAGE TEMPERATURE	OPERATING TEMPERATURE	SOLDERING TEMPERATURE
80	10 mA	-50°C to +130°C	-40°C to 105°C	N/A

\* CAPACITANCE 12 pF (TYP) @ 80 V